



U.S. Serial No. 09/414,226
Chang 7-20-10

S/B Chua
1-25-02

IN THE UNITED STATES
PATENT AND TRADEMARK OFFICE

Patent Application

Inventor(s): Chorng-Ping Chang
Chien-Shing Pai
Thi-Hong-Ha Vuong

Case: 7-20-10

Serial No.: 09/414,226

Group Art Unit: 2811

Filing Date: October 7, 1999

Examiner: Donghee Kang

Title: Semiconductor Device with Tapered Gate and Process For
Fabricating the Device

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

AMENDMENT AND REQUEST FOR RECONSIDERATION
PURSUANT TO 37 C.F.R. § 1.111

This reply is in response to the Official Action mailed June 15, 2001.

IN THE CLAIMS

- B'*
Sub
D'
1. (amended) A semiconductor device comprising:
a semiconductor substrate in which a source, drain and channel are
formed;
a gate formed on a gate dielectric layer formed on the semiconductor
substrate;
spacers adjacent to the gate wherein the gate and spacers are formed in
a trench formed in a layer of dielectric material formed on the substrate